

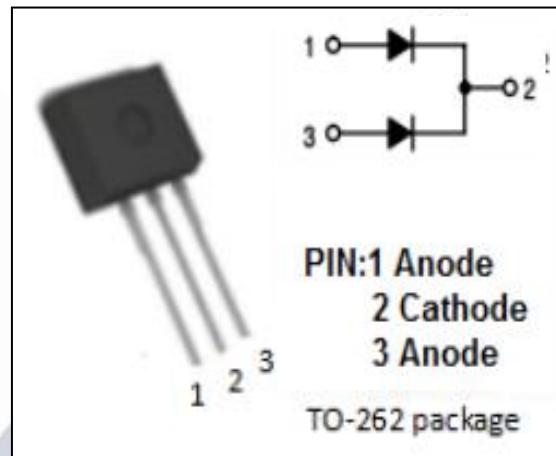
Ultra fast Rectifier

STTH2003CR
FEATURES

- With TO-262(I2PAK) packaging
- Low leakage current, low power loss, high efficiency
- High frequency operation
- High current capability
- Low stored charge majority carrier conduction
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Switching power supply
- High frequency inverters
- Freewheeling diodes
- Reverse battery protection
- Polarity protection applications


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM} V_{RWM} V_R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	300	V
$I_{F(AV)}$	Average Rectified Forward Current @ $T_c=92^\circ\text{C}$	20	A
I_{FSM}	Nonrepetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60Hz)	110	A
T_J	Junction Temperature	-65~175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~175	$^\circ\text{C}$

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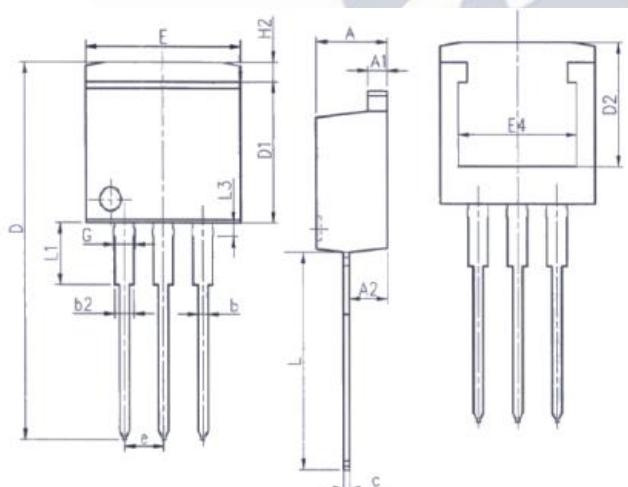
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th,j-c}$	Thermal Resistance,Junction to Case	2.5	°C/W

ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$) (Pulse Test: Pulse Width=300 μs ,Duty Cycle $\leq 2\%$)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F^*	Maximum Instantaneous Forward Voltage	$I_F=10\text{A}; T_c=25^\circ\text{C}$ $I_F=10\text{A}; T_c=125^\circ\text{C}$	1.25 1.0	V
I_R^*	Maximum Instantaneous Reverse Current	$V_R=V_{RWM}; T_c=25^\circ\text{C}$ $V_R=V_{RWM}; T_c=125^\circ\text{C}$	20 300	μA
t_{rr}	Maximum Reverse Recovery Time	$I_F=1\text{A}; V_R=30\text{V}; -di_F/dt=-50\text{A}/\mu\text{s}$	35	ns

DIMENSIONAL DRAWING



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.22	1.42
A2	2.47	2.87
b	0.70	0.97
b2	1.17	1.42
c	0.28	0.53
D	23.20	24.02
D1	8.38	8.90
D2	6.00	-

Unit: mm		
Symbol	Min.	Max.
E	9.90	10.39
E4	7.30	-
e	2.54BSC	
G	1.25	1.50
H2	-	1.31
L	13.34	14.10
L1	3.30	4.06
L3	0.95	1.15

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Fig. 1: Peak reverse recovery current versus dI_F/dt (90% confidence, per diode).

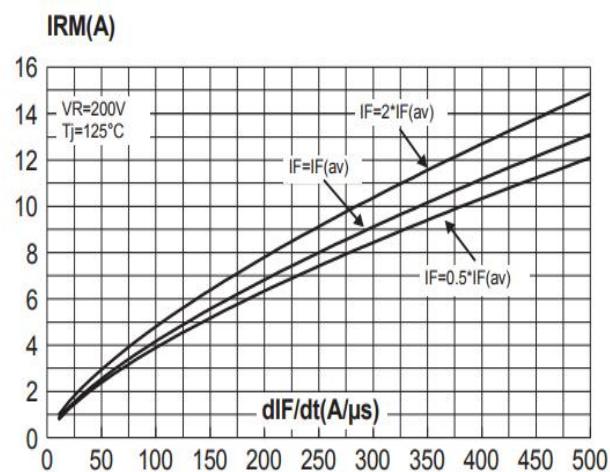


Fig. 2: Forward voltage drop versus forward current (maximum values, per diode).

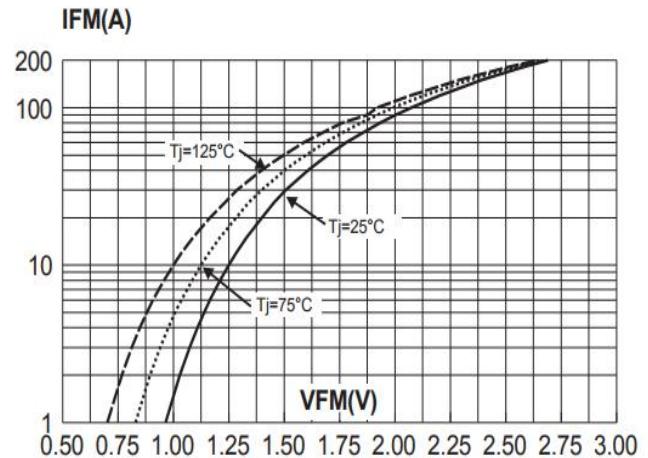


Fig. 3: Reverse recovery time versus dI_F/dt (90% confidence, per diode).

